

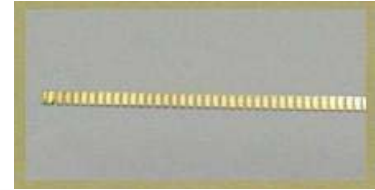
INPHENIX

Gain Chip

IPSGC0801/ IPSGC1301/ IPSGC1501 (820nm/1310nm/1550nm)

Feature

- 820 nm, 1310nm and 1550nm Wavelengths
- Quantum Well Active Layer Structure
- Broad Bandwidth and High Output Power
- Excellent AR and HR Optical Coatings
- Available as Chip, Chip on Carrier, and Chip on Submount.



Applications

- Gain Medium for Single FBG Laser and Tunable External Cavity Lasers

IPSGC0801 – 820nm nm Gain Chip Specifications @($T_{chip}=25^{\circ}C$)

Parameter	Specifications				Conditions
	Min.	Typ.	Max.	Unit	
ASE Peak Wavelength λ	800	820	840	nm	
Threshold Current I_{th}		10		mA	CL-CL
Slope Efficiency		40		%	CL-CL
ASE Bandwidth		25		nm	HR-AR

IPSGC1301 –1310 nm Gain Chip Specifications @($T_{chip}=25^{\circ}C$)

Parameter	Specifications				Conditions
	Min.	Typ.	Max.	Unit	
ASE Peak Wavelength λ	1290	1310	1330	nm	
Threshold Current I_{th}		12		mA	CL-CL
Slope Efficiency		25		%	CL-CL
ASE Bandwidth		40		nm	HR-AR

INPHENIX

IPSGC1501 –1550 nm Gain Chip Specifications @ (T_{chip} =25°C)

Parameter	Specifications				Conditions
	Min.	Typ.	Max.	Unit	
ASE Peak Wavelength λ	1510	1550	1590	nm	
Threshold Current I _{th}		15		mA	CL-CL
Slope Efficiency		20		%	CL-CL
ASE Bandwidth		40		nm	HR-AR

Part Numbering Structure



Model-

- IPSGC0801: 820 nm Gain Chip
- IPSGC1301: 1310 nm Gain Chip
- IPSGC1501: 1550 nm Gain Chip

Assembly Options:

- Bare Chip
- Chip On Carrier
- Chip On Submount

Example: IPSGC0801: 820 nm gain chip.

Corporate Office

250 North Mines Rd
 Livermore, CA 94551
 Tel: 925.606.8809
 Fax: 925.606.8810
www.inphenix.com

All information contained herein is believed to be accurate and is subject to change without notification. No responsibility is assumed. Please contact InPhenix for more information. InPhenix and the InPhenix logo are trademarks of InPhenix Inc.. All rights are reserved.